Transverse thermoelectric effect in \( a \)-axis inclinedly oriented SnSe thin films

(SUPPLEMENTARY MATERIAL)

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Fig. S1. (a) XRD pattern of the $a$-axis oriented SnSe thin film ($\beta=0^\circ$) deposited on MgO single crystal substrate. (b) The left hand is the sketch map of the XRD measurement.

Fig. S2. (a) HRTEM cross-sectional image of the SnSe thin film on MgO single crystal substrate; (b) the magnified HRTEM image of the film part, showing that the $a$-lattice parameter is about 11.52 Å